DISTINCTIVE CHARACTERISTICS

- Logic voltage levels compatible with TTL
- Three-state output buffers and common I/O
- I_{CC} Max., as low as 100 mA

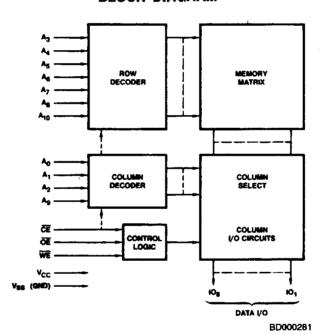
- tAA/tACS as low as 70 ns
- Power-Down mode (ISB as low as 15 mA)

GENERAL DESCRIPTION

The Am9128 is a 16,384-bit Static Random = Access Read-write Memory organized as 2048 words of 8 bits. It uses fully static circuitry, requiring no clocks or refresh to operate. Directly TTL-compatible inputs and outputs and operation from a single +5 V supply simplify system

designs. Common data I/O pins using three-state outputs are provided. The Am9128 is available in an industry-standard 24-pin DIP package with 0.6-inch pin row spacing. The Am9128 uses the JEDEC standard pinout for byte-wide memories (compatible to 16K EPROMs).

BLOCK DIAGRAM



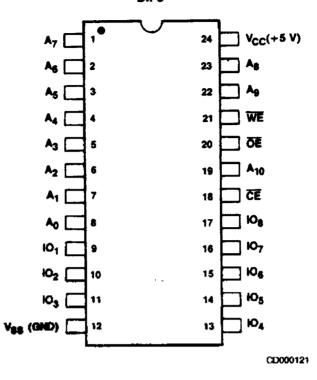
PRODUCT SELECTOR GUIDE

Part Nu	Am9128-70	Am9128-90	Am9128-10	Am9128-12	Am9128-15	Am9128-20	
Maximum Access Time (ns)		70	90	100	120	150	200
Maximum Operat-	0 to 70°C	140	N/A	120	N/A	100	140
ing Current (mA)	-55° to 125°C	N/A	180	N/A	150	150	150
Maximum Standby	0° to 70°C	30	N/A	15	N/A	15	30
Current (mA)	-55° to 125°C	N/A	30	N/A	30	30	30

Publication # Rev. Amendment 02050 E /0 Issue Date: January 1989

CONNECTION DIAGRAMS Top View

DIPs



Note: Pin 1 is marked for orientation.

METALLIZATION AND PAD LAYOUT

Address Designators							
External	Internal						
A3	AX ₀						
A4	AX ₁						
A ₅	AX ₂						
Ae	AX3						
A ₇	AX4						
A ₈	AX ₅						
A ₁₀	AX ₆						
A ₀	AY ₀						
A ₁	AY ₁						
A ₂	AY ₂						
A ₉	AY ₃						



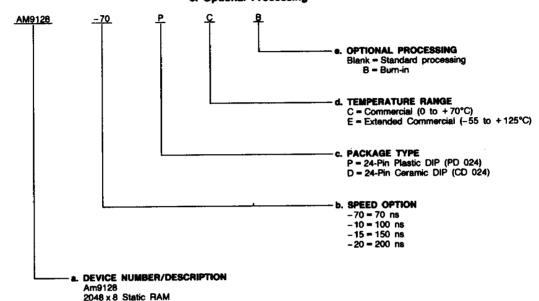
DIE SIZE: 0.162" x 0.240"

ORDERING INFORMATION

Standard Products

AMD standard products are available in several packages and operating ranges. The order number (Valid Combination) is formed by a combination of: **a. Device Number**

- b. Speed Option (if applicable)
- c. Package Type
- d. Temperature Range
- e. Optional Processing



Valid Combinations							
AM9128-70							
AM9128-10	PC, DC, DCB, DE,						
AM9128-15	DEB						
AM9128-20							

Valid Combinations

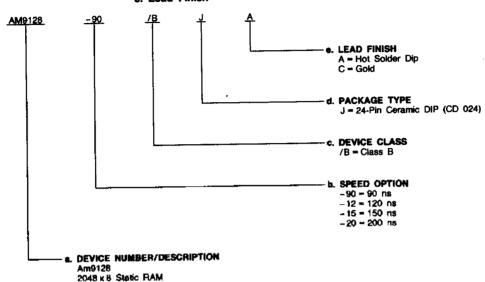
Valid Combinations list configurations planned to be supported in volume for this device. Consult the local AMD sales office to confirm availability of specific valid combinations, to check on newly released combinations, and to obtain additional data on AMD's standard military grade products.

ORDERING INFORMATION

APL Products

AMD products for Aerospace and Defense applications are available in several packages and operating ranges. APL (Approved Products List) products are fully compliant with MIL-STD-883C requirements. The order number (Valid Combination) for APL products is formed by a combination of: a. Device Number

- b. Speed Option (if applicable)
- c. Device Class
- d. Package Type
- e. Lead Finish



Valid Combinations					
AM9128-90					
AM9128-12	/BJA, /BJC				
AM9128-15	75374, 7530				
AM9128-20					

Valid Combinations

Valid Combinations list configurations planned to be supported in volume for this device. Consult the local AMD sales office to confirm availability of specific valid combinations or to check for newly released valid combinations.

Group A Tests

Group A tests consist of Subgroups 1, 2, 3, 7, 8, 9, 10, 11

PIN DESCRIPTION

A₀ - A₁₀ Addresses (Input)

The 10-bit field presented at the address inputs selects one of the 2048 memory locations to be read from — or written into — via the data lines.

I/O₁-I/O₈ Data in/Out Port (Input/Output)

If WE is LOW, the data represented on the I/O lines can be written into the selected memory location. If WE is HIGH, the I/O lines represent the data read from the selected memory location.

CE Chip Enable (input, Active LOW)

Read and Write cycles can be executed only when CE is LOW.

WE Write Enable (Input, Active LOW)

Data is written into the memory if WE is LOW and read from the memory if WE is HIGH.

OE Output Enable (Input, Active LOW)

Read cycles can be executed only when OE is LOW.

ABSOLUTE MAXIMUM RATINGS (Note 11)

Storage Temperature	65 to +150°C
Ambient Temperature with	
Power Applied	55 to +125°C
Supply Voltage	0.5 V to +7.0 V
Signal Voltage with	
Respect to Ground	3.0 V to +7.0 V
Power Dissipation	1.0 W
DC Output Current	

^{*}Maximum ratings are to be for system design reference, parameters given may not be 100% tested by AMD.

Stresses above those listed under ABSOLUTE MAXIMUM RATINGS may cause permanent device failure. Functionality at or above these limits is not implied. Exposure to absolute maximum ratings for extended periods may affect device reliability.

OPERATING RANGES (Note 3)

Commercial (C) Devices	
Ambient Temperature (T _A)	0 to +70°C
Supply Voltage (Voc)	
Military* (M) and Extended Commer	
Case Temperature (T _A)	55 to +125°C
Supply Voltage (VCC)	+4.5 V to +5.5 V

Operating ranges define those limits between which the functionality of the device is guaranteed.

DC CHARACTERISTICS over operating ranges unless otherwise specified (for APL Products, Group A, Subgroups 1, 2, 3 are tested unless otherwise noted) (Note 3)

					128- 9 0 128-10	Am91	128-15	Am91	28-70 28-12 28-20	
Parameter Symbol	Parameter Description	Test Conditions			Max.	Min.	Max.	Min.	Max.	Unit
10н	Output HIGH Current	V _{OH} = 2.4 V	2.4 V V _{CC} = 4.5 V	-2		-2		-2		mA
loL	Output LOW Current	V _{OL} = 0.4 V	VCC = 4.5 V	4		4		4		mA
VIH	Input HIGH Voltage			2.0	V _{CC} + 1.0	2.0	VCC + 1.0	2.0	V _{CC} + 1.0	٧
VIL	Input LOW Voltage			-0.5	0.8	-0.5	0.8	-0.5	8.0	٧
I _{IX}	Input Load Current	V _{SS} ≪ V _I ≪ V _{CC}			10		10		10	μA
loz	Output Leakage Current	V _{SS} ≤ V _O ≤ V _{CC} Output Disabled			10		10		10	μA
CiN	Input Capacitance (Note 12)	Test Frequency = 1.0 MHz.			6		6		6	ρF
C _{I/O}	Input/Output Capacitance (Note 12)	TA = 25°C, All pins at 0	V _{CC} ≈ 5.0 V		7	7	7		7	
		May Vot 7E < Vo.	COM'L		120		100	140		
loc	V _{CC} Operating Supply Current	Max. V _{CC} , Œ ≤ V _{IL} Outputs Open	MIL/E- COM'L		180		150	150		mA.
			COM*L		15		15	30		
lse	Automatic CE Power Down Current	Max. V _{CC} , CE > V _H	MIL/E- COM'L		30		30	30		mA
		V	COM'L		15		15	30		
IPO	Peak Power On Current (Note 12)	V _{CC} = GND to V _{CC} Max. CE ≥ V _{IH} (Note 2)	MIL/E- COM'L		30		30	30		mA

- Notes: 1. The internal write time of the memory is defined by the overlap of CE LOW and WE LOW. Both signals must be LOW to initiate a write and either signal can terminate a write by going HIGH. The data input setup and hold timing should be referenced to the rising edge of the signal that terminates the write.

 - that terminates the write.

 2. A pull up resistor to V_{CC} on the CE input is required during power up to keep the device deselected, otherwise I_{PC} will exceed values given.

 3. For test and correlation purposes, ambient temperature is defined as the "Instant-on" case temperature.

 4. At any given temperature and voltage condition, t_{HZ} is less than t_{LZ}.

 5. WE is HIGH for read cycle.

 6. Device is continuously selected, CE = V_{IL}.

 7. Address valid prior to or coincident with CE transition LOW.

 8. OE = V_{IL}.

 9. C_L = 30 pF.

 10. Transition is measured from 1.5 V on the input to V_{OH} = 500 mV and V_{OL} + 500 mV on the outputs using the load shown in Switching Test Circuite. C_L = 5. pF.
 - 11. The products described by this specification include internal circuitry designed to protect input devices from damaging accumulations of static charge. It is suggested, nevertheless, that conventional precautions be observed during storage, handling, and use to avoid exposure to excessive voltages.
 - 12. The parameter is guaranteed by characterization, but is not tested.

SWITCHING CHARACTERISTICS over operating ranges unless otherwise specified (for APL Products, Group A. Subgroups 9, 10, 11 are tested unless otherwise noted.)

Am9128-70, -90, -10

	T	1		Am91	26-70	Am91	28-90	Am9128-10		l .
No.	Parameter Parameter Symbol Description			Min.	Max.	Min.	Max.	Min.	Max.	Unit
RE	AD CYCLE									
1	t _{RC}	Read Cycle Time		70		90	<u> </u>	100	ļ <u></u>	ns.
2	tACC	Address Access Time	(Note 9)		70		90		100	ns
3	1ACS	Chip Select Access Ti	ne (Note 9)		70		90		100	ns
		Output Enable Time	COMIL		40	<u> </u>	N/A	ļ <u> </u>	50	лз
4	to∈	(Note 9)	MIL	I	N/A		50		N/A	
5	фн	Output Hold Time from	Address Change	5		5		5		na na
6	laz	Output in Low-Z from CE (Notes 4, 10, 12)		5		5	<u> </u>	5	<u> </u>	ns ns
7	tchz	Output in Hi-Z from CE (Notes 4, 10, 12)			35		40		40	ne
8	touz	Output in Low-Z from OE (Notes 4, 10, 12)		5	<u> </u>	5		5		ns
9	tonz	Output in Hi-Z from OE (Notes 4, 10, 12)			30		35	<u> </u>	35	na
10	teu teu	Chip Selection to Power-Up Time (Note 12)		0		0		0		ns
11	ten	Chip Deselection to Power-Down Time (Note 12)			40		45	<u> </u>	50	N8
	RITE CYCLE									
12	twc	Write Cycle Time		70		90	I	100	<u> </u>	ns
	 ""	Chip Selection to	0 to +70°C	60		N/A		90	1	l na
13	\$CW	End of Write (Note 1)	-55 to -125°C	N/A		80		N/A	<u> </u>] "3
14	las	Address Setup Time		5	1	10		10		na
15	twp	Write Pulse Width (No	ote 1)	40	†	55	T.	60		ns
16	· ····	Write Recovery Time		5	T -	5		5	T	ne
17	twr	Oata Setuo Time		30		35		40	1	ns
	tos	Data Hold Time		5	1	5	1	5		A18
18	tOH _	Output in Low-Z from WE (Notes 4, 10, 12)		5	1	5	T	5	1	ns
19	MLZ	Output in Hi-Z from V			30	†	35	1	35	ne
20	t _{AW}	Address to End of W		65	1	80	 	80	1	ns

Notes: See notes following DC Characteristics table.

SWITCHING CHARACTERISTICS (Cont'd.)

Am9128-12, -15, -20

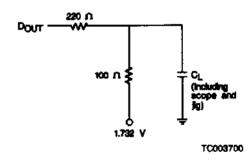
		Parameter Description		Am91	26-12	Am9	126-15	Am9	28-20	
No.	Parameter Symbol			Min.	Max.	Min.	Max.	Min.	Max.	Unit
AE	AD CYCLE									
1	\$RC	Read Cycle Time		120		150	<u> </u>	200		nas
2	tacc	Address Access Time (Not	e 9)		120		150	<u> </u>	200	nas
3	tacs	Chip Select Access Time (Note 9)		120	L	150		200	nes
		Output Enable Time	COMFL		N/A		80	<u> </u>	70	ns
4	tOE (Note 9)	MIL		70		70		80		
5	tОН	Output Hold Time from Ad	dress Change	5		5		5		ns
6	*CLZ	Output in Low-Z from CE (Notes 4, 10, 12)		5		5	<u> </u>	5		па
7	tonz	Output in Hi-Z from CE (Notes 4, 10, 12)			50	I	55		55	រាន
8	touz	Output in Low-Z from OE (Notes 4, 10, 12)		5		5]	- 5		ns
9	[‡] OHZ	Output in Hi-Z from OE (Notes 4, 10, 12)			45	[50		50	ns
10	teu	Chip Selection to Power-Up Time (Note 12)		0		0		0		ns
11	tpp	Chip Deselection to Power-Down Time (Note 12)			55		60	l	60	ns.
WF	TE CYCLE									
12	fwc	Write Cycle Time		120		150		200		ns.
		Chip Selection to	COM'L	N/A		120	T	150		
13	tow	End of Write (Note 1)	MIL	105		130		160		l Page
14	las	Address Setup Time	•	10		20		20		Lts
15	twe	Write Pulse Width (Note 1)	70		85		100	1	ns
16	twn	Write Recovery Time		5	1	5	[5		fr#9
17	los	Data Setup Time		45		50	T	60		ns
18	toH	Data Hold Time		5		- 5		5		n#
19	twiz	Output in Low-Z from WE (Notes 4, 10, 12)		5		5		- 6		na.
20	WHZ	Output in Hi-Z from WE (f	Votes 4, 10, 12)		50		50		50	ПВ
21	1aw	Address to End of Write		105		120		120		na

Notes: See notes following DC Characteristics table.

SWITCHING TEST CONDITIONS

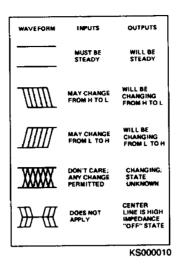
Input Puise Levels	.4 to 2.4
Input Rise and Fall Times	10 ns
Input Timing Reference Levels	1.4 V
Output Timing Reference Levels	1.4 V

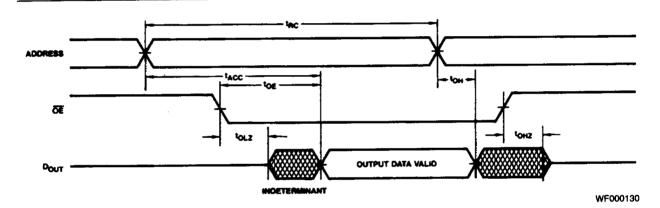
SWITCHING TEST CIRCUIT



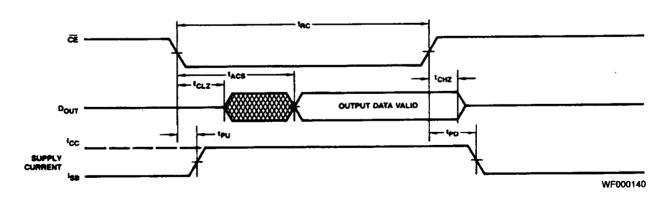
4-86 Am9128

SWITCHING WAVEFORMS KEY TO SWITCHING WAVEFORMS





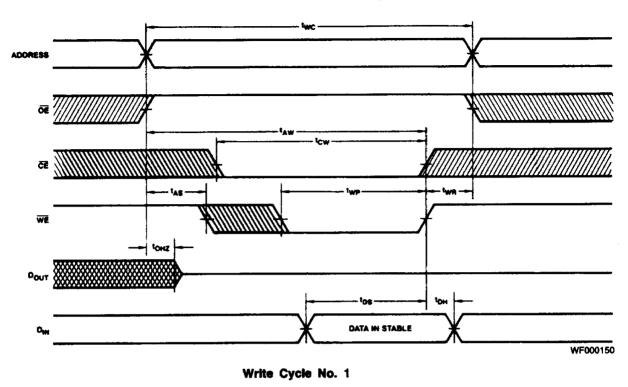
Read Cycle No. 1 (Notes 5, 6)

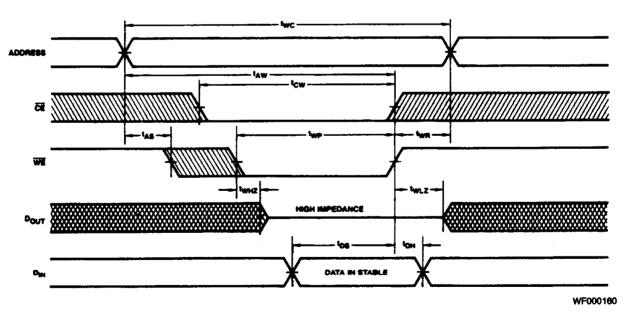


Read Cycle No. 2 (Notes 5, 7, 8)

Notes: See notes following DC Characteristics table.

SWITCHING WAVEFORMS (Cont'd.)





Write Cycle No. 2 (Notes 7, 8)

Notes: See notes following DC Characteristics table.

TYPICAL PERFORMANCE CURVES

